Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		150		mA	V_D=12V;R_L=3ohms;T_j=+25ºC
Gate- trigger voltage	V_{GT}	0.70	2.5		V	V_D=12V;R_L=3ohms;T_j=+25ºC
Peak negative voltage	V_{GRM}		5		V	

Delay time	t_d		3.0	2.5	μs	I_{TM}=1000A; V_D=67%V_{DRM} Gate pulse: V_G=30V; R_G=10ohms; t_r=0.1μs; tp=20μs
Turn-off time (with V_R = -5 V)	t_q		70		μs	I_{TM} =1500 A; di/dt =- 25A/μs; V_R =50 V; dv/dt=30V/μs ; V_D= 67%V_{DRM};T_j=125ºC
Reverse recovery charge	Q_{rr}				μC	I_{TM}=1500 A;di/dt=-10A/μs; V_R=50 V; T_j=125ºC

Operating temperature	T_j	-40	+125		ºC	
Storage temperature	T_{stg}	-40	+140		ºC	
Thermal resistance - junction to case	$R_{\Theta(j-c)}$		0.016		ºC/W	Double sided cooled
Thermal resistance - case to heatsink	$R_{\Theta(c-s)}$		0.005		ºC/W	Double sided cooled
Mounting force	F	25	31	28	kN	
Weight	m			0.65	kg	

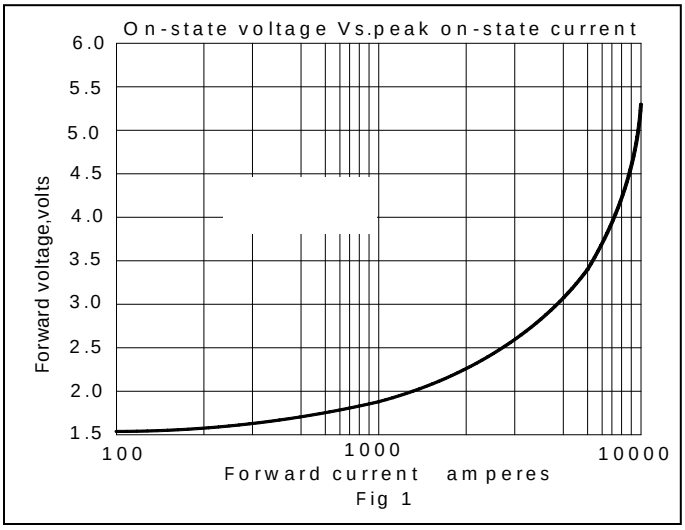


Fig 1

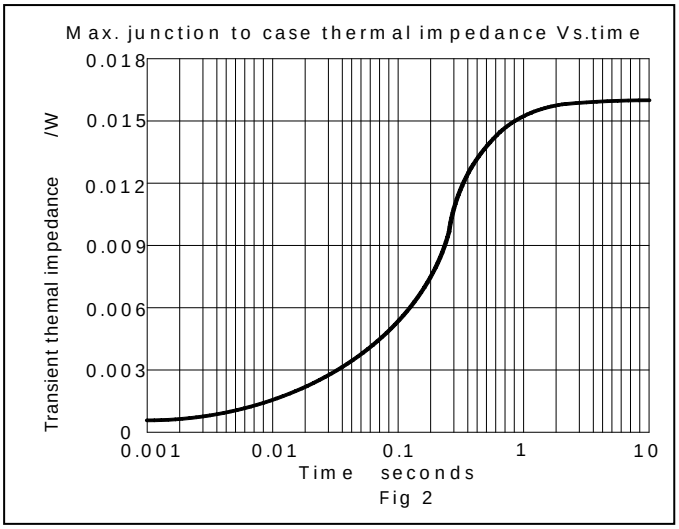


Fig 2

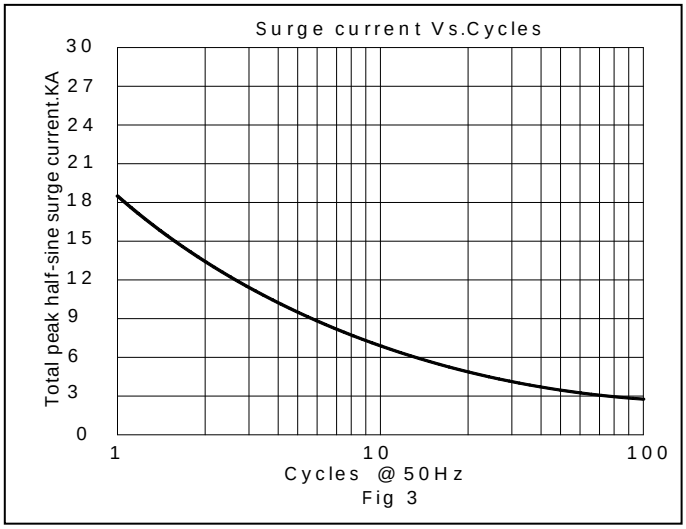


Fig 3

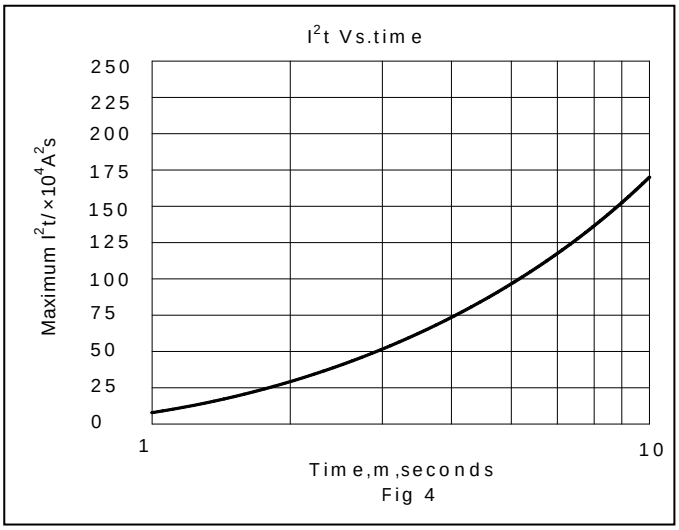
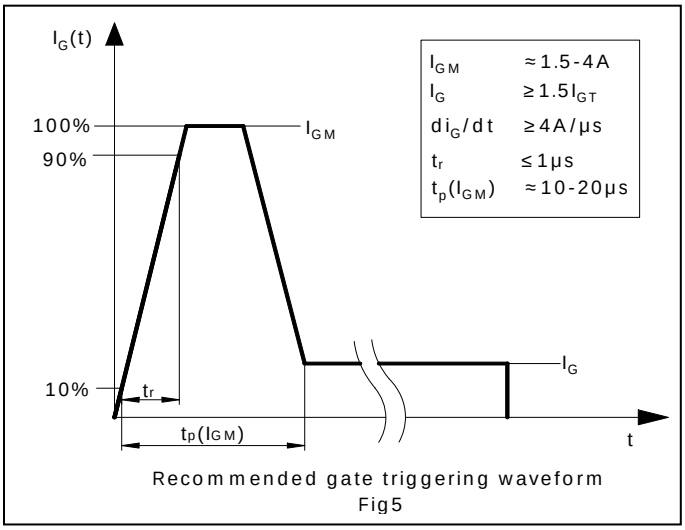


Fig 4



Recommended gate triggering waveform
Fig5

